

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	234	"kuwazawa".in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/25 15:29
S2	9	"kuwazawa".in. and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/31 14:36
S3	4	("6579764" "6462370").pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 13:58
S4	5	("5104819" "6204126" "6380035" "5497018" "5908311").pn.	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/06/01 14:10
S5	11	(first adj capacitor) same (second adj capacitor) same (non-volatile with transistor)	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/10/25 14:15
S6	4	(first adj capacitor) same (second adj capacitor) same (non-volatile with transistor) and ono	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/10/25 14:15
S7	24	(first adj capacitor not electrode) same (second adj capacitor not electrode) and (non-volatile with transistor)	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/10/25 14:16
S8	21	(first adj capacitor not electrode) same (second adj capacitor not electrode) and (non-volatile with transistor) not S5	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/10/25 14:16
S9	11	(first adj capacitor) same (second adj capacitor) same ((non-volatile with transistor) or (split adj gate))	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/10/25 14:16
S10	4	(first adj capacitor) same (second adj capacitor) same ( (split adj gate))	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/10/25 14:16
S11	6	(first adj capacitor not electrode) same (second adj capacitor not electrode) and ((split adj gate) or split-gate)	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/10/25 14:16
S12	177	(first adj capacitor not electrode) same (second adj capacitor not electrode) and ("same" with substrate)	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/06/10 13:59

S13	130	(first adj capacitor not electrode) same (second adj capacitor not electrode) and ("same" with substrate) and (memory or transistor)	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/06/10 11:43
S14	9	(first adj capacitor not electrode) same (second adj capacitor not electrode) same ("same" with substrate) and (memory or transistor)	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/10/25 14:16
S15	17	(first adj capacitor not electrode) same (second adj capacitor not electrode) same ("same" with substrate)	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/10/25 14:16
S16	7	(US-4399522-\$ or US-5523970-\$ or US-6898105-\$ or US-RE35810-\$ or US-5886377-\$ or US-6486530-\$ or US-6590473-\$).did.	USPAT	OR	ON	2005/06/10 12:17
S17	2	((US-4399522-\$ or US-5523970-\$ or US-6898105-\$ or US-RE35810-\$ or US-5886377-\$ or US-6486530-\$ or US-6590473-\$).did.) and ONO	USPAT	OR	ON	2005/06/10 12:17
S18	2	"JP 03105981 A"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 13:47
S19	2	"JP 04348568 A"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 13:51
S20	2	"JP 05021808 A"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 13:53
S21	2	"JP 09092736 A"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 13:54
S22	2	"JP 09321227 A"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 13:55

S23	2	"JP 10154792 A"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 13:56
S24	13729	257/296,316,324,532,640.ccls. 438/257-267,238,585.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 13:59
S25	177	(first adj capacitor not electrode) same (second adj capacitor not electrode) and ("same" with substrate)	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/06/10 13:59
S26	10	S24 and S25	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/10/25 14:16
S27	0	(first adj capacitor) same (second adj capacitor) same (non-volatile with transistor) and @pd>"20050610"	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/10/25 14:15
S28	0	(first adj capacitor) same (second adj capacitor) same (non-volatile with transistor) and ono and @pd>"20050610"	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/10/25 14:15
S29	0	(first adj capacitor not electrode) same (second adj capacitor not electrode) and (non-volatile with transistor) and @pd>"20050610"	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/10/25 14:16
S30	11	(first adj capacitor) same (second adj capacitor) same (non-volatile with transistor)	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/10/25 14:16
S31	0	(first adj capacitor not electrode) same (second adj capacitor not electrode) and (non-volatile with transistor) not S30 and @pd>"20050610"	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/10/25 14:16
S32	0	(first adj capacitor) same (second adj capacitor) same ((non-volatile with transistor) or (split adj gate)) and @pd>"20050610"	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/10/25 14:16
S33	0	(first adj capacitor) same (second adj capacitor) same ( (split adj gate)) and @pd>"20050610"	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/10/25 14:16
S34	3	(first adj capacitor not electrode) same (second adj capacitor not electrode) and ((split adj gate) or split-gate) and @pd>"20050610"	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/10/25 14:16

S35	1	(first adj capacitor not electrode) same (second adj capacitor not electrode) same ("same" with substrate) and (memory or transistor) and @pd>"20050610"	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/10/25 14:16
S36	1	(first adj capacitor not electrode) same (second adj capacitor not electrode) same ("same" with substrate) and @pd>"20050610"	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/10/25 14:16
S37	14405	257/296,316,324,532,640.ccls. 438/257-267,238,585.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/25 14:16
S38	185	(first adj capacitor not electrode) same (second adj capacitor not electrode) and ("same" with substrate)	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/10/25 14:16
S39	0	S37 and S38 and @pd>"20050610"	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/10/25 14:17
S40	4	S34 S35 S36	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/10/25 14:17
S41	0	(memory and transistor and (first adj capacitor) and (second adj capacitor) and (lower adj electrode) and (first adj dielectric) and (upper adj electrode) and (second adj dielectric) and (thermal adj oxidation) and (nitride adj film) and (oxide adj film) and (first adj thermal) and cvd and (second adj thermal)). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/25 15:32